

N-channel TrenchMOS standard level FET 11 September 2012

**Product data sheet** 

#### **Product profile** 1.

### 1.1 General description

Standard level N-channel MOSFET in a SOT226 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 1.2 Features and benefits

- AEC Q101 compliant •
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

### **1.3 Applications**

- 12 V Automotive systems
- Electric and electro-hydraulic power steering •
- Motors, lamps and solenoid control •
- Start-Stop micro-hybrid applications
- Transmission control •
- Ultra high performance power switching •

### 1.4 Quick reference data

Table 1. Qu	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	-	120	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	349	W
Static charact	teristics	1					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11		-	1.5	1.8	mΩ
Dynamic cha	racteristics						
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; Fig. 13; Fig. 14		-	48.2	-	nC

#### Quick reference data Table 1

[1] Continuous current is limited by package.

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### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G - UFI A
mb	D	mounting base; connected to drain	I 2 3 I 2PAK (SOT226)	mbb076 S

### 3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BUK7E1R8-40E	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226		

### 4. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7E1R8-40E	BUK7E1R8-40E

### 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	40	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	120	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	120	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	1278	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	349	W
T <sub>stg</sub>	storage temperature			-55	175	°C

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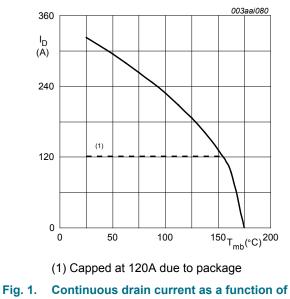
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Symbol	Parameter	Conditions		Min	Мах	Unit
Tj	junction temperature			-55	175	°C
Source-drai	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	1278	А
Avalanche r	ruggedness					,
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 120 \text{ A};  \text{V}_{sup} \leq 40  \text{V};  \text{R}_{GS} = 50  \Omega; \\ \text{V}_{GS} &= 10  \text{V};  \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 3} \end{split}$	[2][3]	-	1021	mJ

[1] Continuous current is limited by package.

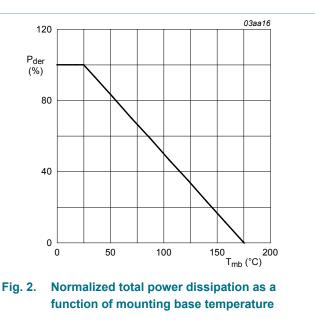
[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.



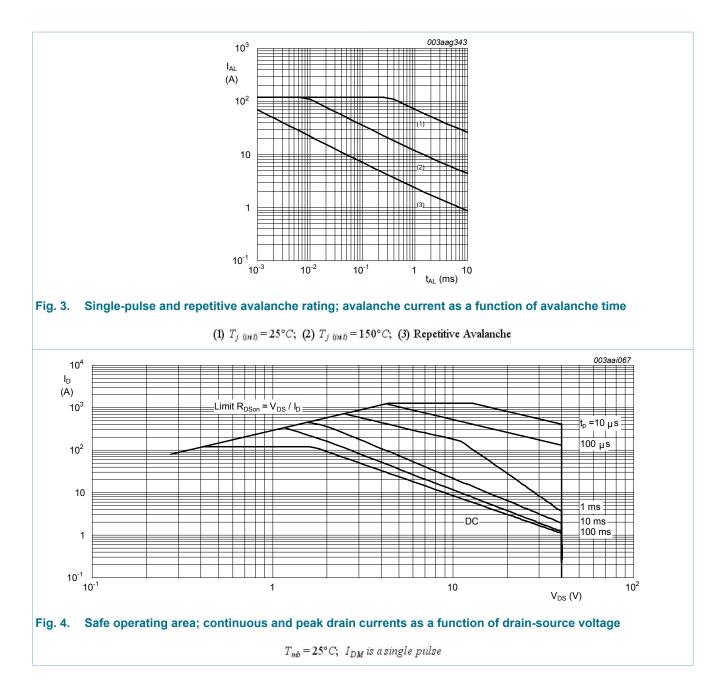
mounting base temperature

 $V_{GS} \ge 10V$ 



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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### 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.43	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	vertical in still air	-	65	-	K/W

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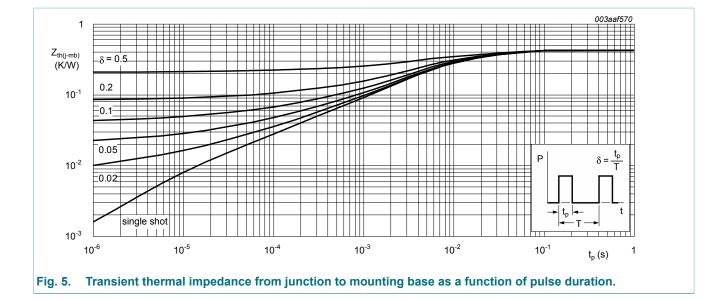
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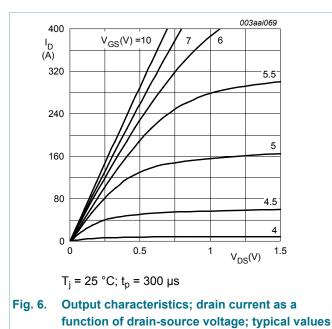
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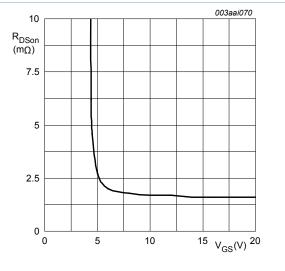
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·	I			
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	40	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	36	-	-	V
V <sub>GS(th)</sub> gate-source threshold voltage	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.5	V
	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10	1	-	-	V	
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.25	3	μA
		$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	1.5	1.8	mΩ
	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	-	3.4	mΩ
Dynamic ch	naracteristics	· · · · ·				
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V;	-	145	-	nC
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	35.7	-	nC
Q <sub>GD</sub>	gate-drain charge	1	-	48.2	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	8500	11340	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	1620	1950	pF
C <sub>rss</sub>	reverse transfer capacitance		-	985	1350	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 5 Ω	-	42	-	ns
t <sub>r</sub>	rise time		-	60	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	121	-	ns
t <sub>f</sub>	fall time		-	83	-	ns
-0	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
		from drain lead 6mm from package to centre of die	-	4.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-dra	iin diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	0.77	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 20 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	56	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V	-	94	-	nC





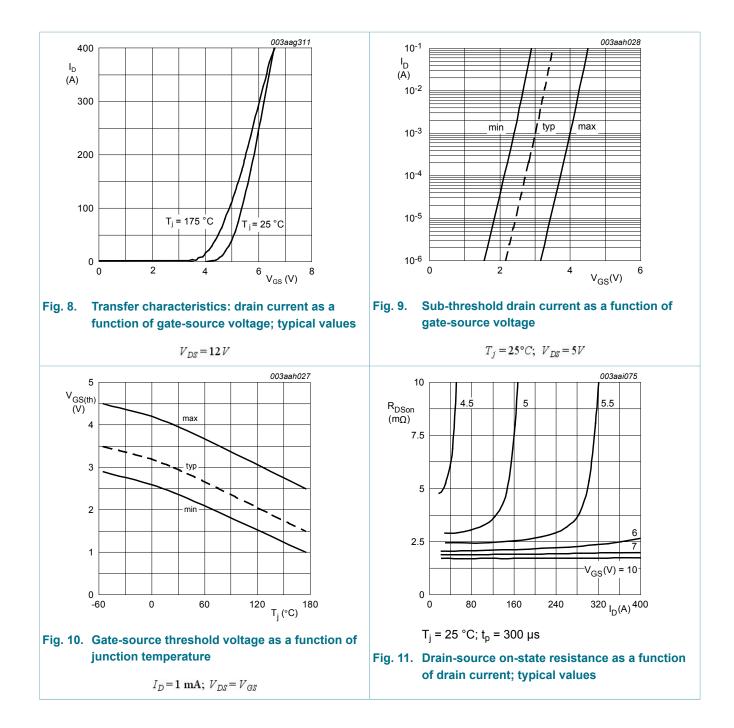


 $T_j = 25^{\circ}C; \ I_D = 25A$ 

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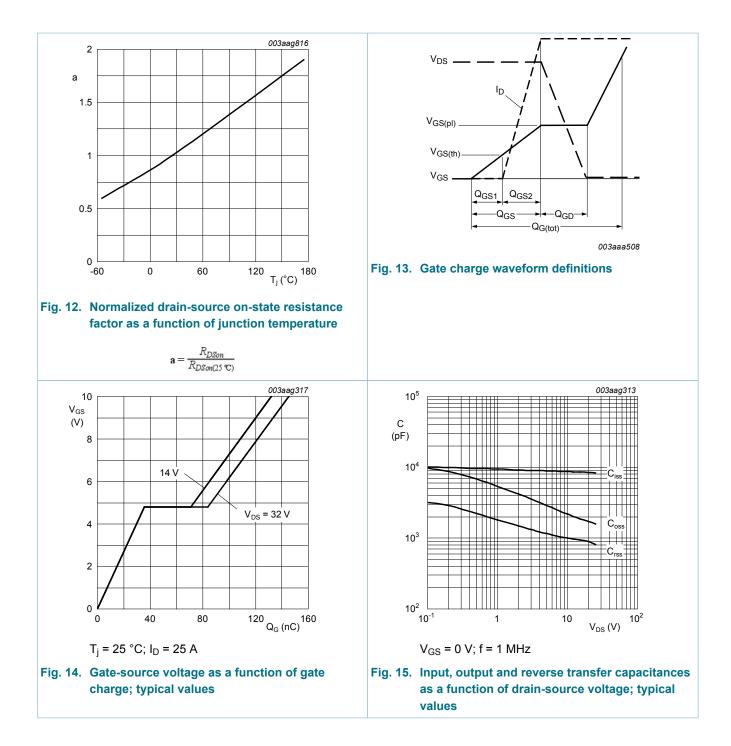
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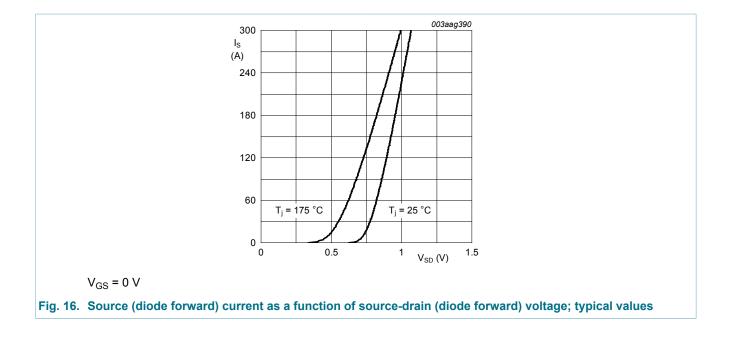
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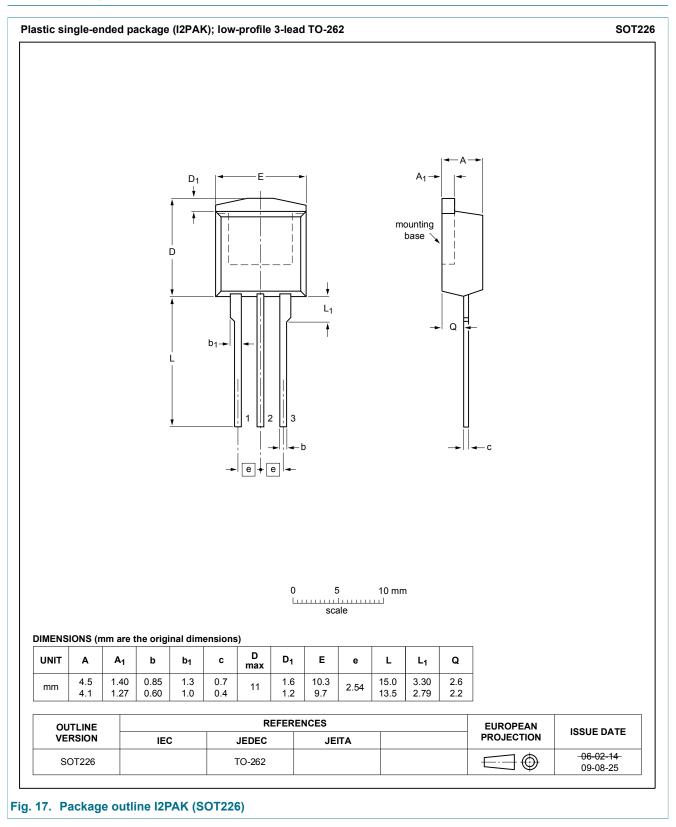


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### 8. Package outline



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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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